

85. (Amended) A device according to claim 84 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

91. (Amended) A device according to claim 90 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

97. (Amended) A device according to claim 96 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

105. (Amended) A device according to claim 102 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

113. (Amended) A device according to claim 110 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

121. (Amended) A device according to claim 118 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

129. (Amended) A device according to claim 126 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

135. (Amended) A device according to claim 134 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

141. (Amended) A device according to claim 140 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

147. (Amended) A device according to claim 146 wherein said semiconductor device comprises transistors selected from the group consisting of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.